

N-Channel Enhancement Mode MOSFET

TDM3424

DESCRIPTION

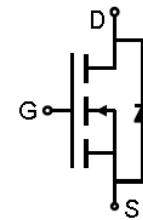
The TDM3424 uses advanced trench technology to provide excellent RDS(ON) and low gate charge .This device is suitable for use as a load switch or in PWM applications.

GENERAL FEATURES

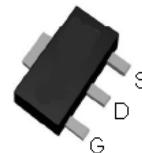
- RDS(ON) < 32mΩ @ VGS=4.5V
RDS(ON) < 23mΩ @ VGS=10V
- High Power and current handling capability
- Lead free product is available
- Surface Mount Package

Application

- PWM applications
- Load switch
- Power management



Schematic diagram



Top View SOT-89

ABSOLUTE MAXIMUM RATINGS($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current @ Continuous (Note 1)	I_D (25°C)	8	A
	I_D (70°C)	6	A
Drain Current @ Current-Pulsed (Note 1)	I_{DM}	20	A
Maximum Power Dissipation ($T_A=25^\circ\text{C}$)	P_D	3.5	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	35	$^\circ\text{C}/\text{W}$
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ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$\text{V}_{\text{GS}}=0\text{V}, \text{I}_D=250\mu\text{A}$	30			V
Zero Gate Voltage Drain Current	I_{DSS}	$\text{V}_{\text{DS}}=24\text{V}, \text{V}_{\text{GS}}=0\text{V}$			1	μA
Gate-Body Leakage Current	I_{GSS}	$\text{V}_{\text{GS}}=\pm 20\text{V}, \text{V}_{\text{DS}}=0\text{V}$			± 100	nA
ON CHARACTERISTICS (Note 3)						
Gate Threshold Voltage	$\text{V}_{\text{GS(th)}}$	$\text{V}_{\text{DS}}=\text{V}_{\text{GS}}, \text{I}_D=250\mu\text{A}$	1	1.9	3	V
Drain-Source On-State Resistance	$\text{R}_{\text{DS(ON)}}$	$\text{V}_{\text{GS}}=4.5\text{V}, \text{I}_D=5\text{A}$		26	32	$\text{m}\Omega$
		$\text{V}_{\text{GS}}=10\text{V}, \text{I}_D=8\text{A}$		20	23	$\text{m}\Omega$
DYNAMIC CHARACTERISTICS (Note 4)						
Input Capacitance	C_{iss}	$\text{V}_{\text{DS}}=15\text{V}, \text{V}_{\text{GS}}=0\text{V}, f=1.0\text{MHz}$		410		PF
Output Capacitance	C_{oss}			70		PF
Reverse Transfer Capacitance	C_{rss}			40		PF
SWITCHING CHARACTERISTICS (Note 4)						
Turn-on Delay Time	$t_{\text{d(on)}}$	$\text{V}_{\text{DS}}=15\text{V}, \text{V}_{\text{GS}}=10\text{V}, \text{R}_{\text{GEN}}=6\Omega, \text{I}_D=1\text{A}$		8		ns
Turn-on Rise Time	t_r			9		ns
Turn-Off Delay Time	$t_{\text{d(off)}}$			14		ns
Turn-Off Fall Time	t_f			4		ns
Total Gate Charge	Q_g	$\text{V}_{\text{DS}}=15\text{V}, \text{I}_D=8\text{A}, \text{V}_{\text{GS}}=4.5\text{V}$		3.8		nC
Gate-Source Charge	Q_{gs}			1.3		nC
Gate-Drain Charge	Q_{gd}			1.6		nC
Body Diode Reverse Recovery Time	T_{rr}	$I_F=8\text{A}, dI/dt=100\text{A}/\mu\text{s}$		12.8		ns
Body Diode Reverse Recovery Charge	Q_{rr}			3.8		nC
DRAIN-SOURCE DIODE CHARACTERISTICS						
Diode Forward Voltage (Note 3)	V_{SD}	$\text{V}_{\text{GS}}=0\text{V}, \text{I}_s=1\text{A}$		0.8	1.1	V

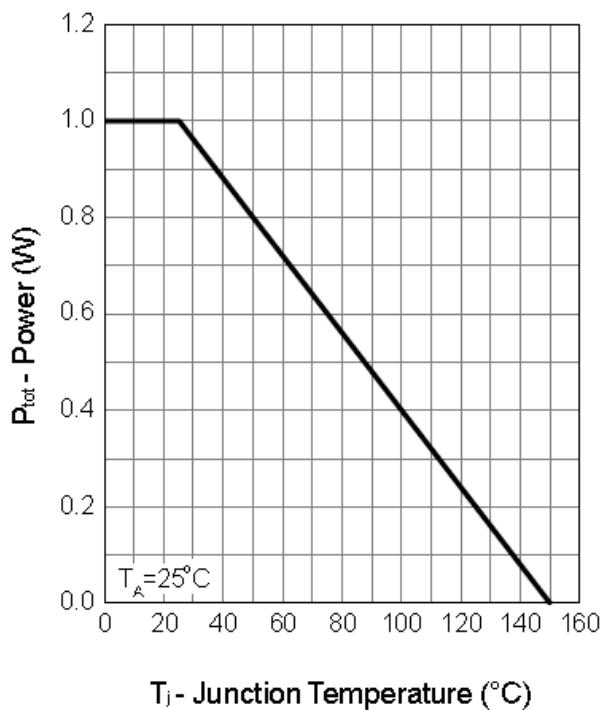
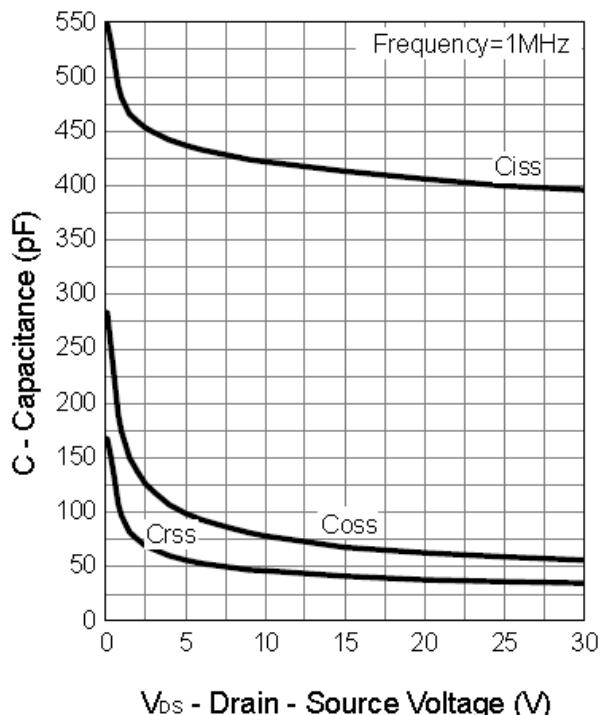
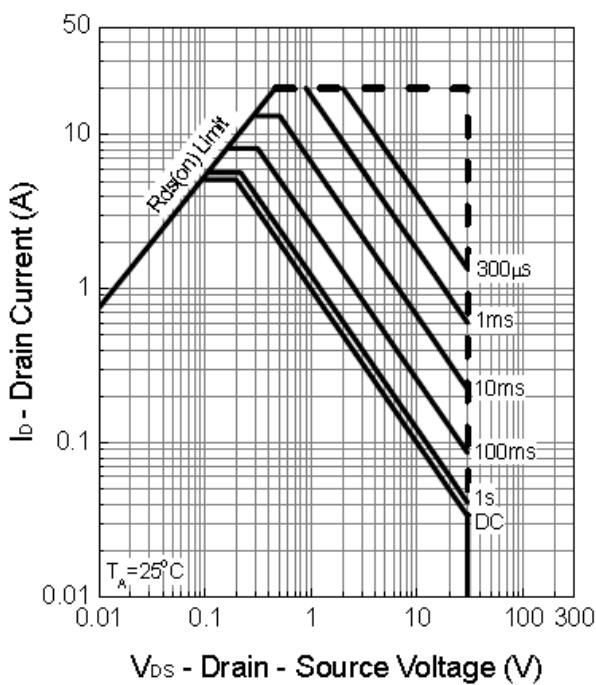
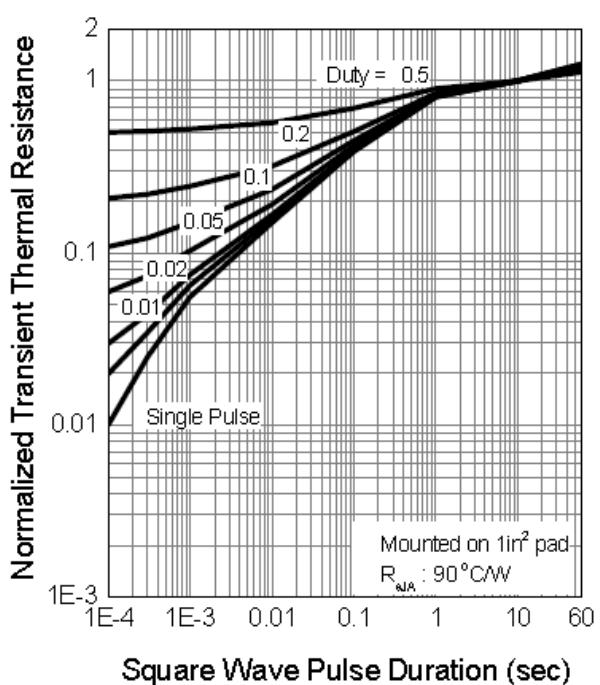
NOTES:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on 1in2 FR4 Board, $t \leqslant 10$ sec.
3. Pulse Test: Pulse Width $\leqslant 300\mu\text{s}$, Duty Cycle $\leqslant 2\%$.
4. Guaranteed by design, not subject to production testing

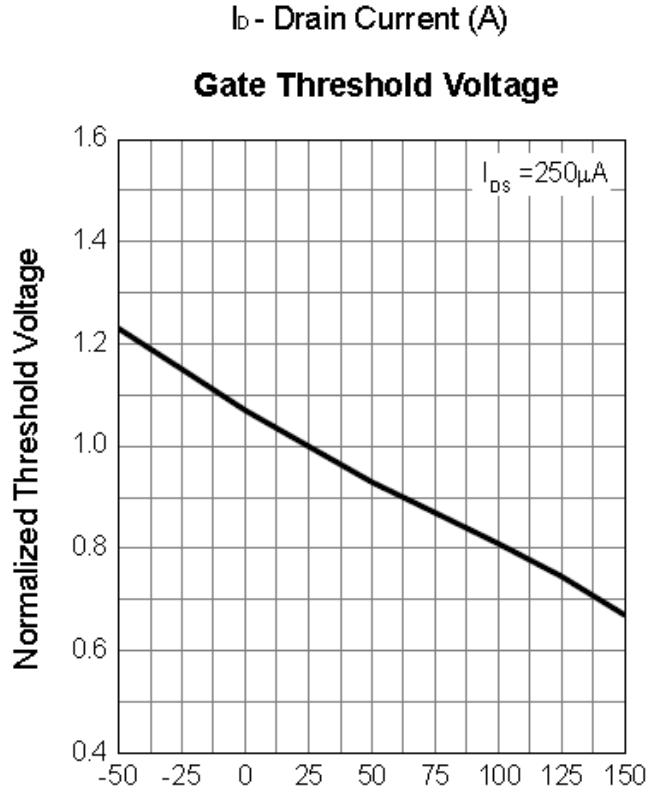
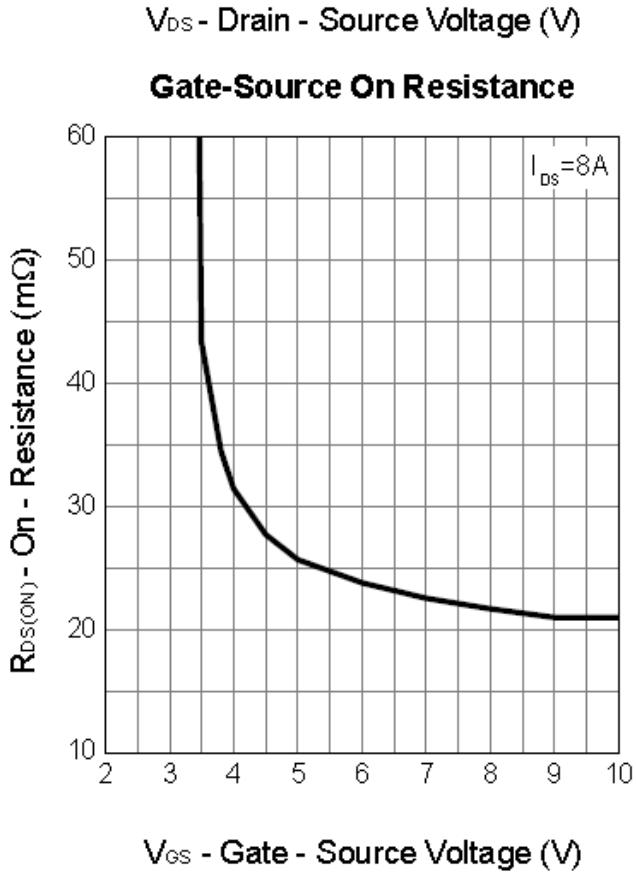
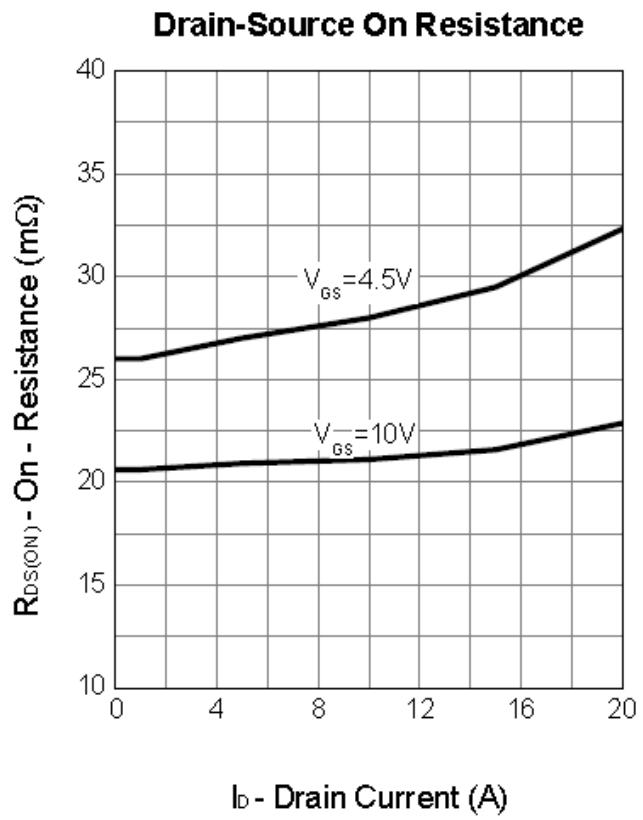
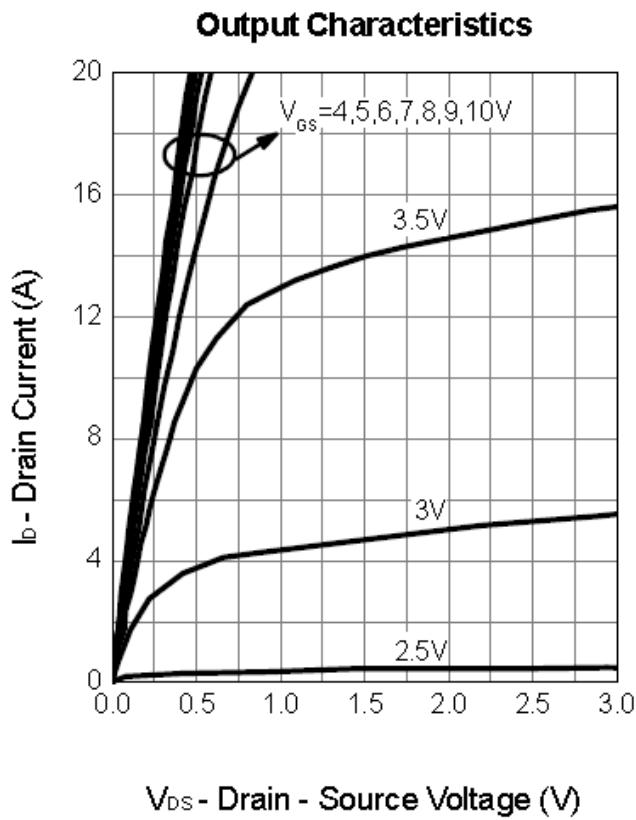
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Typical Operating Characteristics

Power Dissipation**Capacitance****Safe Operation Area****Thermal Transient Impedance**

Typical Operating Characteristics(Cont.)



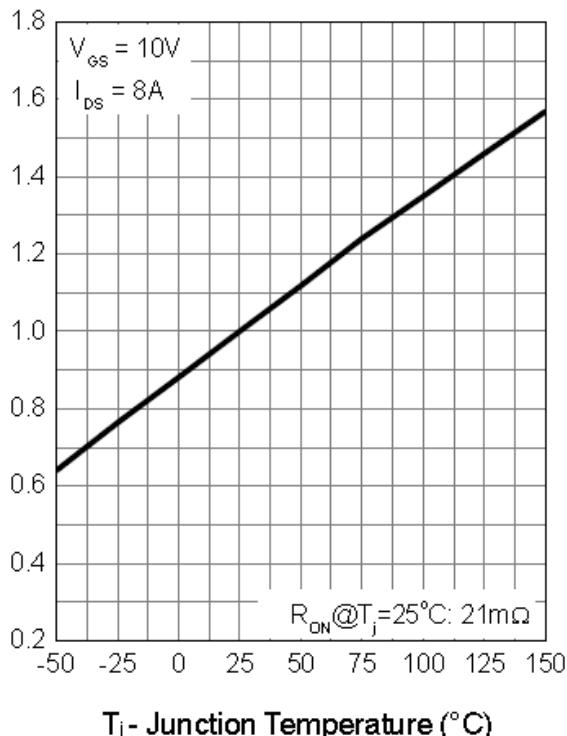
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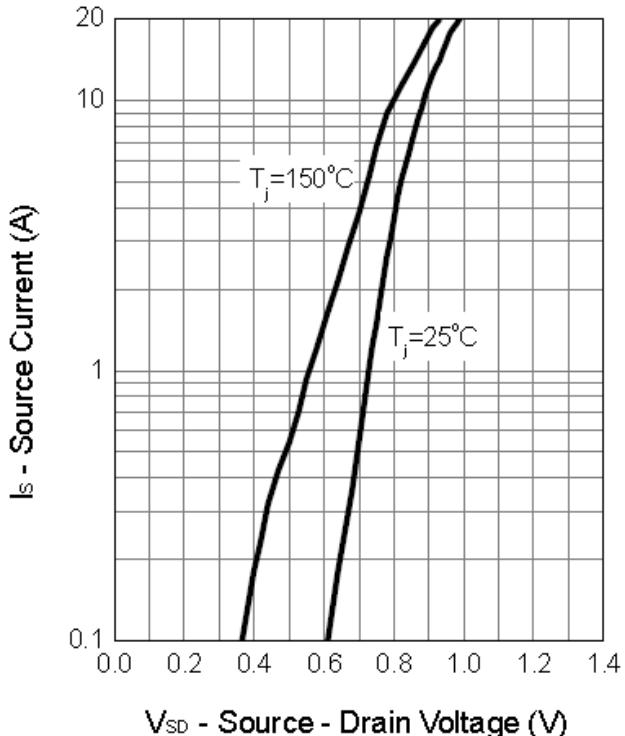
Typical Operating Characteristics (Cont.)

Drain-Source On Resistance

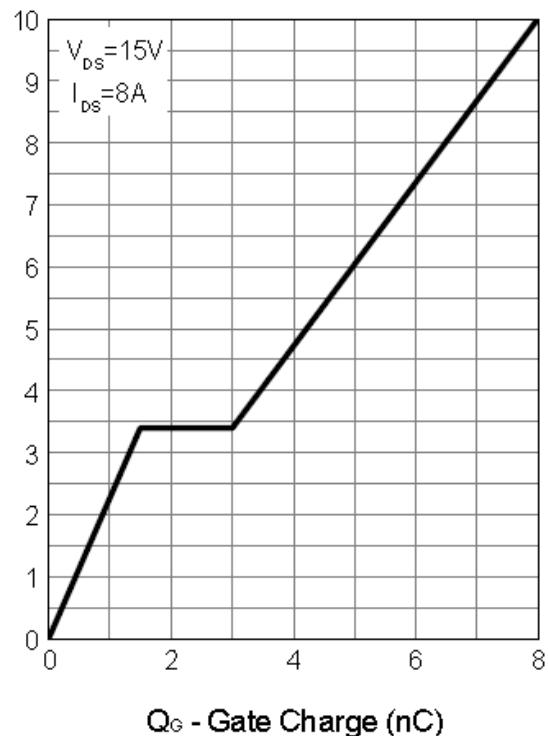
Normalized On Resistance



Source-Drain Diode Forward



Gate Charge

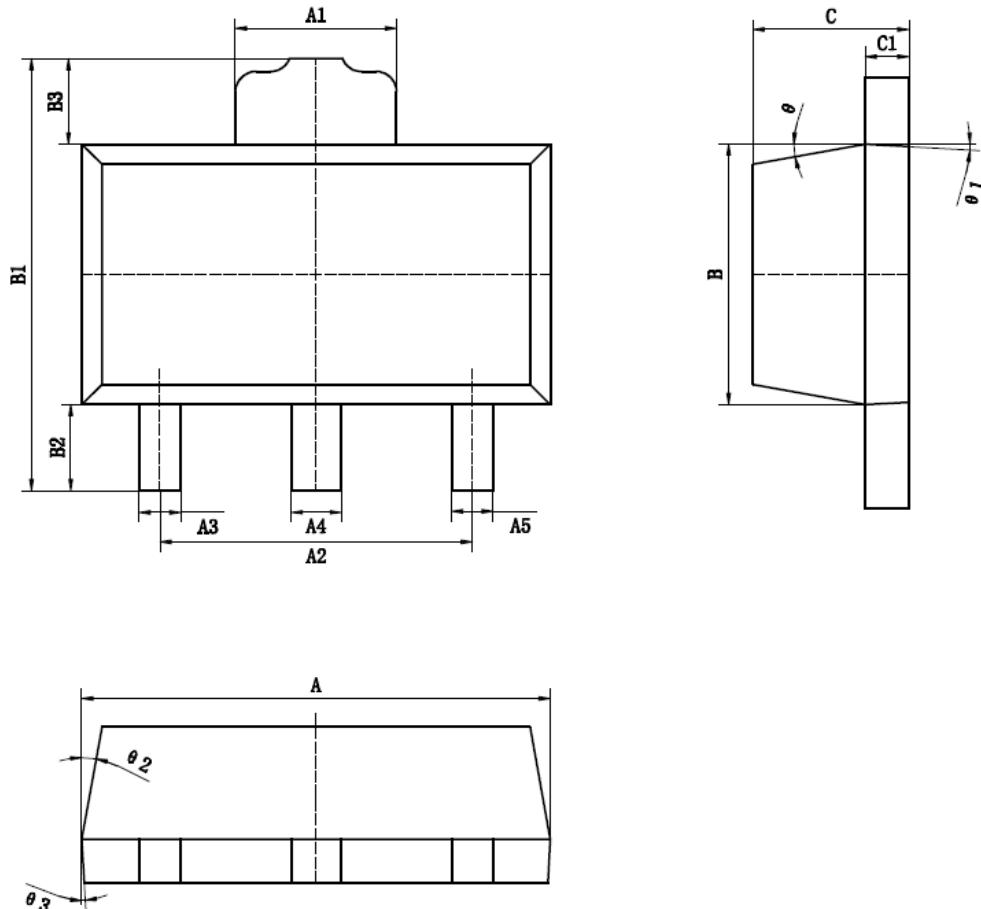
 V_{GS} - Gate - source Voltage (V)

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Package Information

SOT89-3 Package



尺寸 标注	最小(mm)	最大(mm)	尺寸 标注	最小(mm)	最大(mm)
A	4.40	4.60	B3	0.82	0.83
A1	1.65	1.75	C	1.40	1.60
A2	2.95	3.05	C1	0.35	0.45
A3	0.35	0.45	θ	6° TYP4	
A4	0.43	0.53	θ1	3° TYP4	
A5	0.35	0.45	θ2	6° TYP4	
B	2.40	2.60	θ3	3° TYP4	
B1	4.05	4.25			
B2	0.82	0.83			

Design Notes

X-ON Electronics

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